



T-41-61

PHOTOTRANSISTOR

PS4012

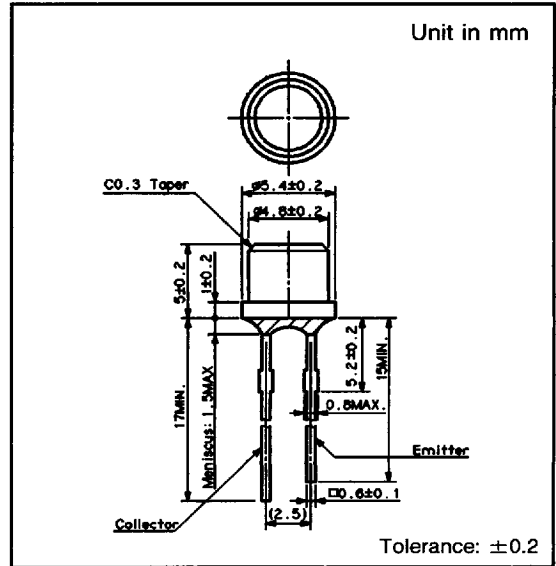
■ **FEATURES**

- FLAT LENS
- 5mm DIA. MOLDED EPOXY TYPE

■ **APPLICATION**

- PHOTODIODE
- PHOTO SWITCH

■ **Package Dimensions**



■ **Absolute Maximum Ratings**

(Ta=25°C)

Item	Symbol	Maximum Ratings	Unit
Collector Dissipation	Pc	100	mW
Collector-Emitter Breakdown Voltage	VCEO	30	V
Emitter-Collector Breakdown Voltage	VECO	5	V
Collector Current	Ic	30	mA
Operating Temperature	Topr	-30 ~ +85	°C
Storage Temperature	Tstg	-30 ~ +100	°C

■ **Electro-Optical Characteristics**

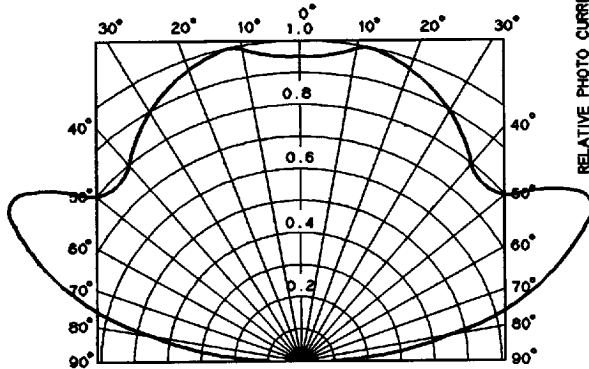
(Ta=25°C)

Item	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-Emitter Dark Current	ICEO	—	—	0.2	μA	VCEP=10V
Photo Current	Ic	0.1	0.5	—	mA	VCE=5V, Ee=1mW/cm ²
Response Time	Leading Time	Tr	—	5	μ sec	VCE=10V Ic=2mA, RL=100Ω
	Trailing Time	Tf	—	5	μ sec	
Peak Sensitivity Wavelength	λp	—	880	—	nm	
Collector-Emitter Saturation Voltage	VCE(sat)	—	0.1	—	V	Ic=0.5mA, Ee=10mW/cm ²

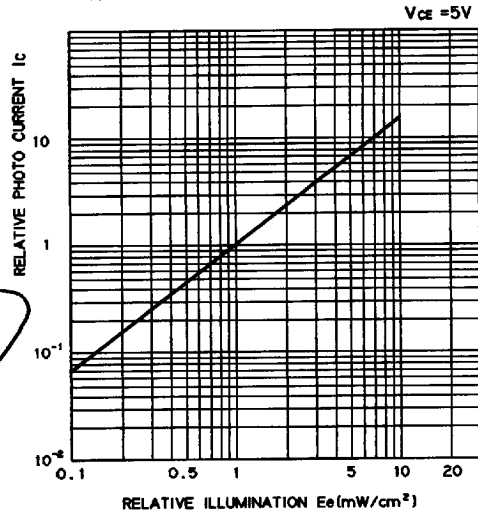
* At color temp. 2856°K standard tungsten filament bulb.

PHOTO-TRANSISTOR

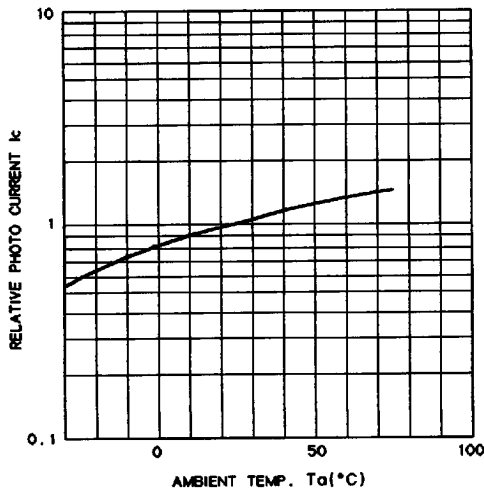
■ DIRECTIVITY CHARACTERISTICS



■ RELATIVE PHOTO CURRENT vs. RADIANT ILLUMINATION

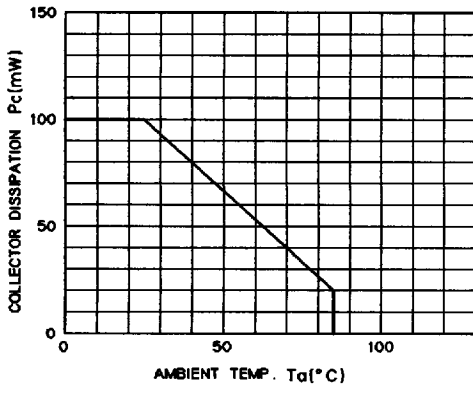


■ PHOTO CURRENT vs. AMBIENT TEMP.

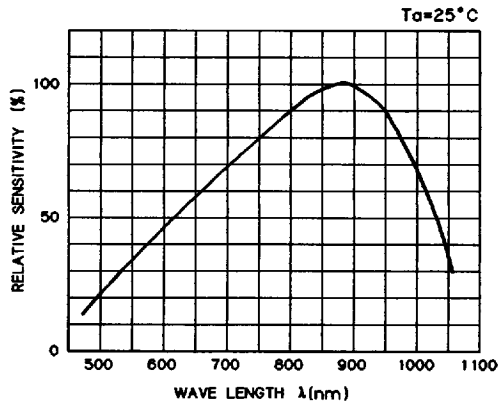


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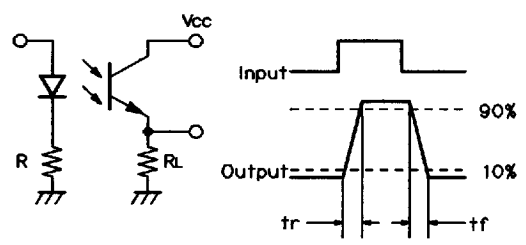
■ COLLECTOR DISSIPATION vs. AMBIENT TEMP.



■ SPECTRAL SENSITIVITY CHARACTERISTICS



■ RESPONSE TIME MEASURING CIRCUIT



■ RESPONSE TIME vs. LOAD RESISTANCE

